

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

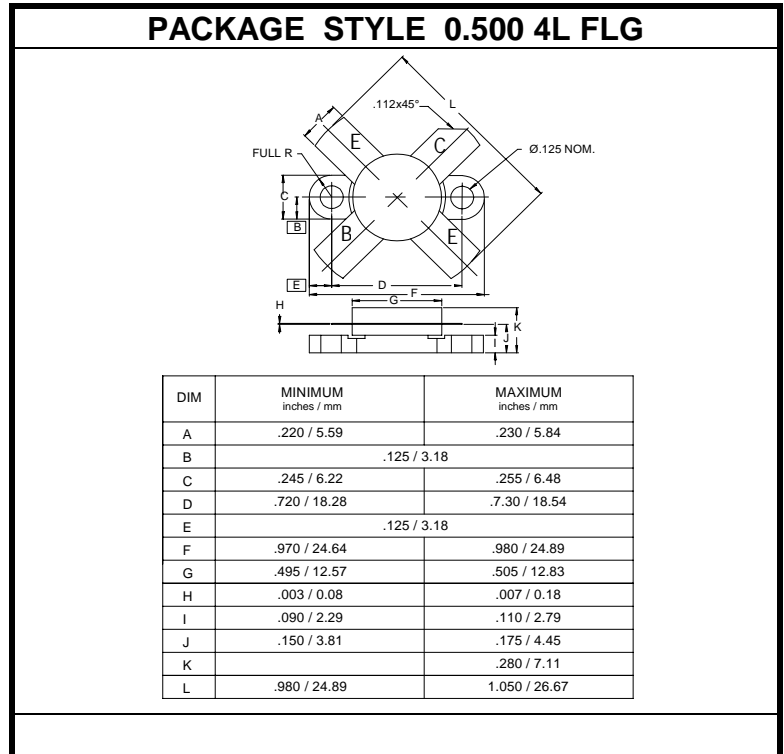
The **ASI TH430** is Designed for SSB and VHF communications. This device utilizes emitter ballasting for improved ruggedness and reliability.

FEATURES:

- $P_G = 14.5$ dB min. at 220 W/30 MHz
- **IMD** = -30 dB max.
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	40 A
V_{CB0}	110 V
V_{CEO}	55 V
V_{EBO}	4.0 V
P_{DISS}	330 W @ T _C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	0.40 °C/W


CHARACTERISTICS T_C = 25° C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 200 mA	55			V
BV_{CES}	I _C = 200 mA	110			V
BV_{EBO}	I _E = 20 mA	4.0			V
I_{CEO}	V _{CE} = 30 V			10	mA
I_{CES}	V _{CE} = 60 V			10	mA
h_{FE}	V _{CE} = 6.0 V I _C = 10 A	15		80	---
C_{ob}	V _{CB} = 50 V f = 1.0 MHz		320	360	pF
G_P	V _{CE} = 50 V I _{CQ} = 150 mA f = 30 MHz	14.5			dB
IMD₃	P _{OUT} = 250 W (PEP)			-30	dBc
η_C		37			%